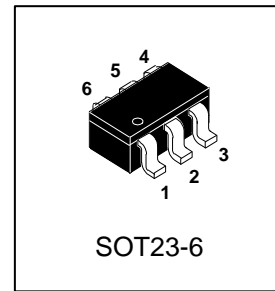


LP2325T1G

20V P-Channel (D-S) MOSFET

1. FEATURES

- Low RDS(ON) trench technology.
- Low thermal impedance.
- Fast switching speed.
- We declare that the material of product compliance with RoHS requirements and Halogen Free.

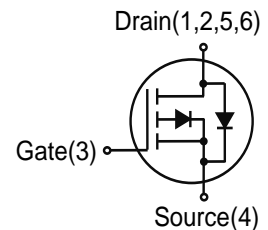


2. APPLICATIONS

- Load Switches
- DC/DC Conversion
- Motor Drives

3. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LP2325T1G	P25	3000/Tape&Reel



4. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit	
Drain-Source Voltage	VDS	-20	V	
Gate-Source Voltage	VGS	± 8		
Continuous Drain Current (Note 1)	ID	-7	A	
Pulsed Drain Current (Note 2)	IDM	-28		
Power Dissipation (Note 1)	PD	TA = 25°C	1.4	W
		TA = 70°C	0.9	
Operating Junction and Storage Temperature Range	TJ , Tstg	-55~+150	°C	

5. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Thermal Resistance, Junction-to-Ambient (Note 1)	RθJA	89	°C/W
Thermal Resistance, Junction-to-Ambient (Note 3)	RθJA	150	°C/W

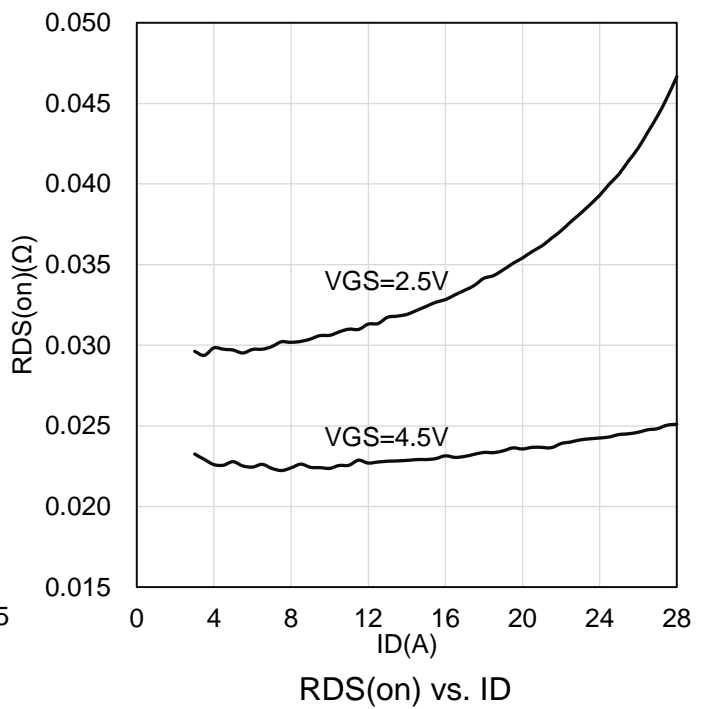
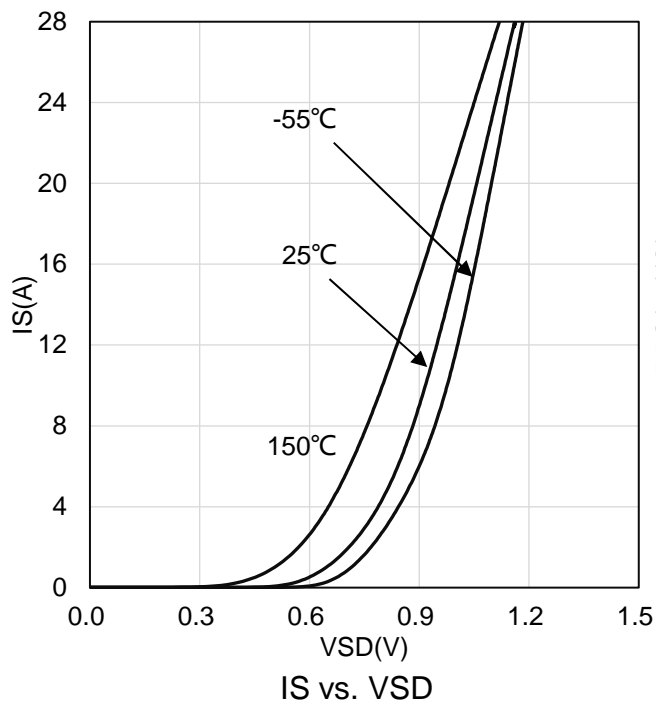
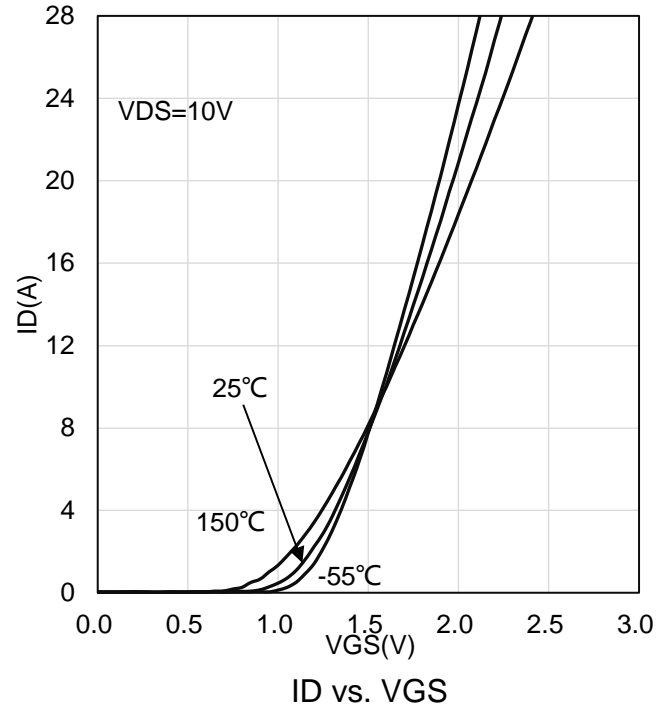
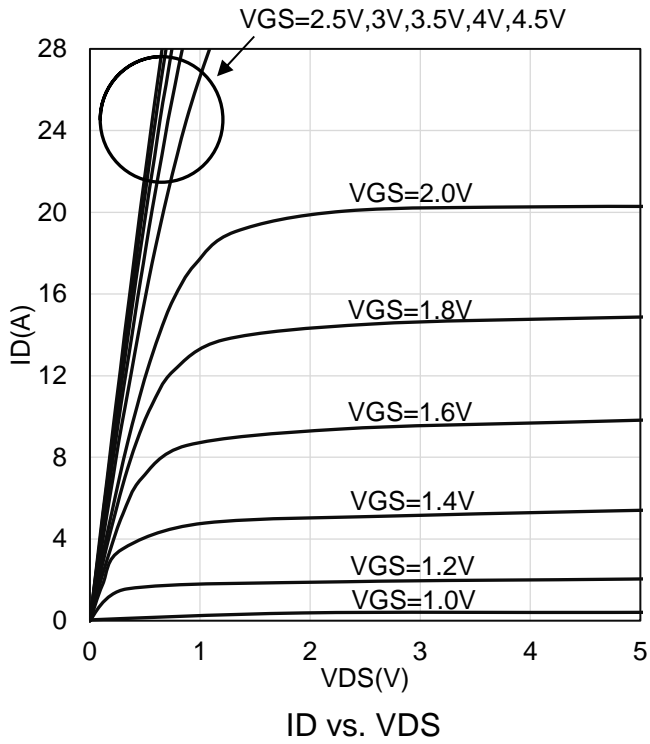
- 1.Surface mounted on "1.5 x 1.5" FR4 board using 1 sq in pad, 2 oz Cu.
- 2.Pulse width limited by maximum junction temperature
- 3.Surface mounted on FR4 board using the minimum recommended pad size.

6. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

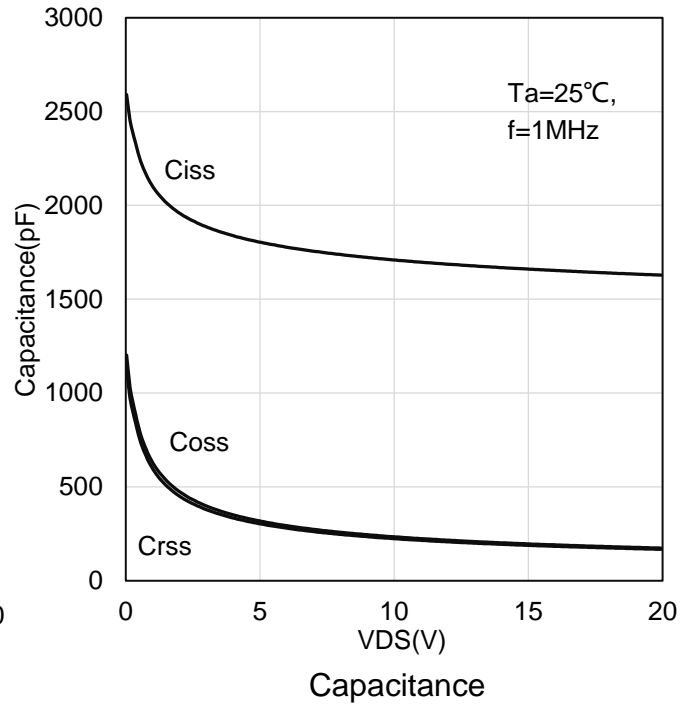
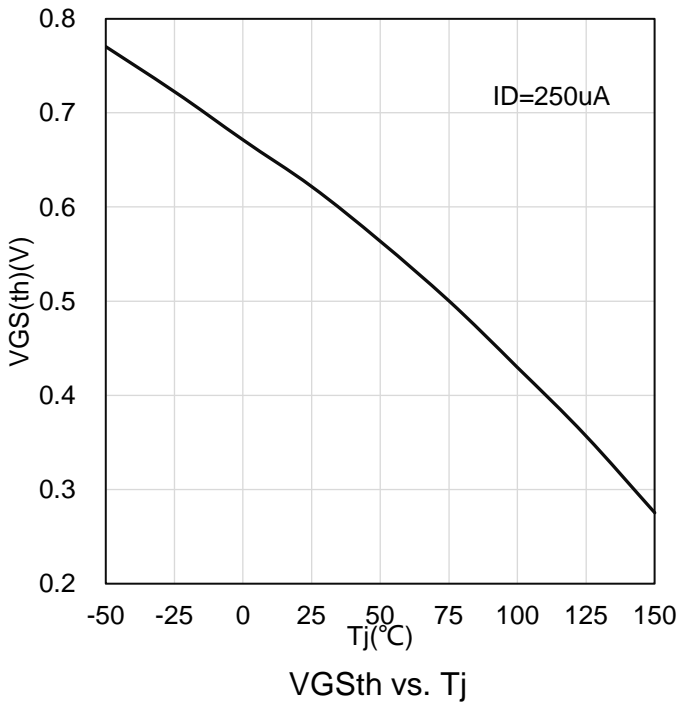
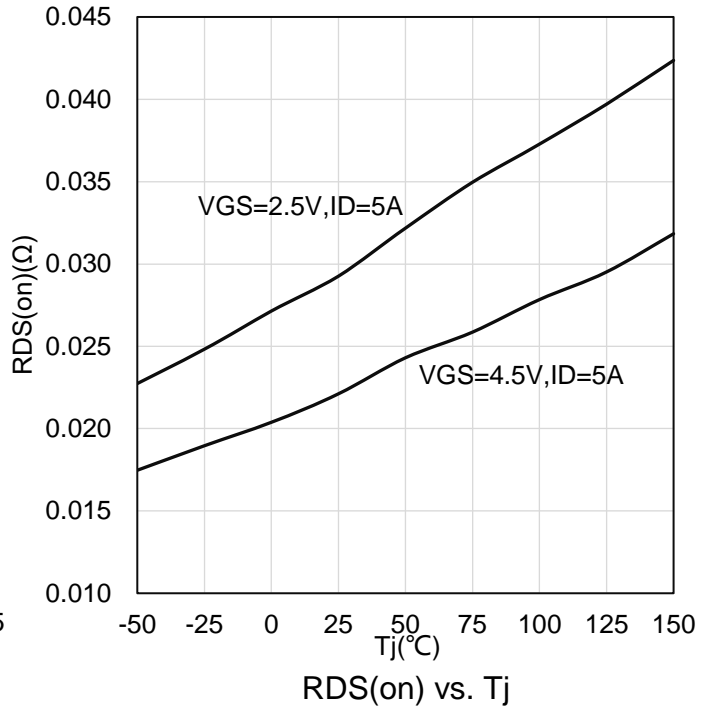
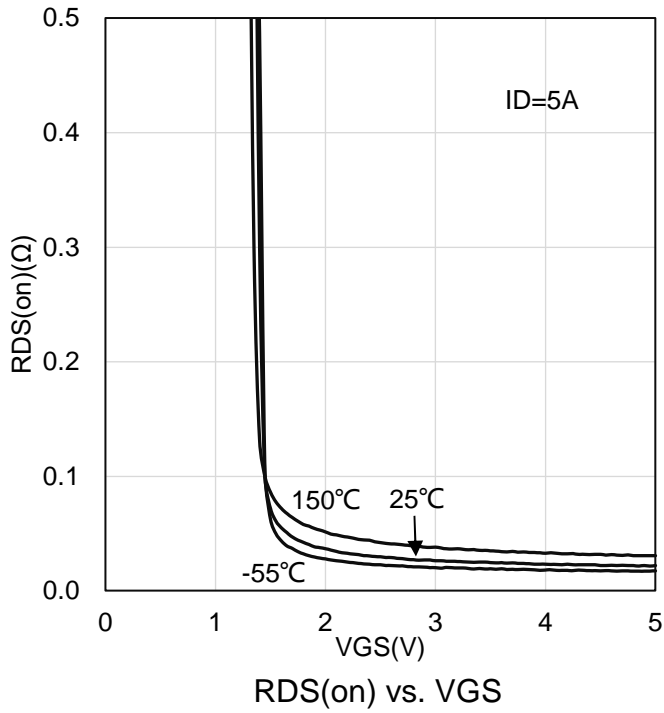
Characteristic	Symbol	Min.	Typ.	Max.	Unit
Static					
Drain-Source Breakdown Voltage (VGS = 0 V, ID = -250 μ A)	V(BR)DSS	-20	-	-	V
Gate Threshold Voltage (VDS = VGS, ID = -250 μ A)	VGS(th)	-0.4	-	-1.2	V
Gate Leakage Current (VDS = 0 V, VGS = \pm 8 V)	IGSS	-	-	\pm 10	μ A
Zero Gate Voltage Drain Current (VDS = -16 V, VGS = 0 V)	IDSS	-	-	-1	μ A
Drain-Source On-Resistance(Note 4) (VGS = -4.5 V; ID = -5 A) (VGS = -2.5 V; ID = -5 A)	RDS(ON)	-	-	28 36	m Ω
Diode Forward Voltage (IS = -2.5 A, VGS = 0 V)	VSD	-	-	-1.3	V
Dynamic					
Total Gate Charge	(VDS = -10 V, VGS = -4.5 V, ID = -7 A)	Qg	-	30	nC
Gate-Source Charge		Qgs	-	4	
Gate-Drain Charge		Qgd	-	6	
Turn-On Delay Time	(VDS = -10 V, RL = 1.4 Ω , ID = -7 A, VGEN = -4.5 V, RGEN = 6 Ω)	td(on)	-	6	ns
Rise Time		tr	-	12	
Turn-Off Delay Time		td(off)	-	85	
Fall Time		tf	-	35	
Input Capacitance	(VDS = -15 V, VGS = 0 V, f = 1 MHz)	Ciss	-	1669	pF
Output Capacitance		Coss	-	198	
Reverse Transfer Capacitance		Crss	-	191	

4. Pulse test: PW \leq 300 μ s ,duty cycle \leq 2%.

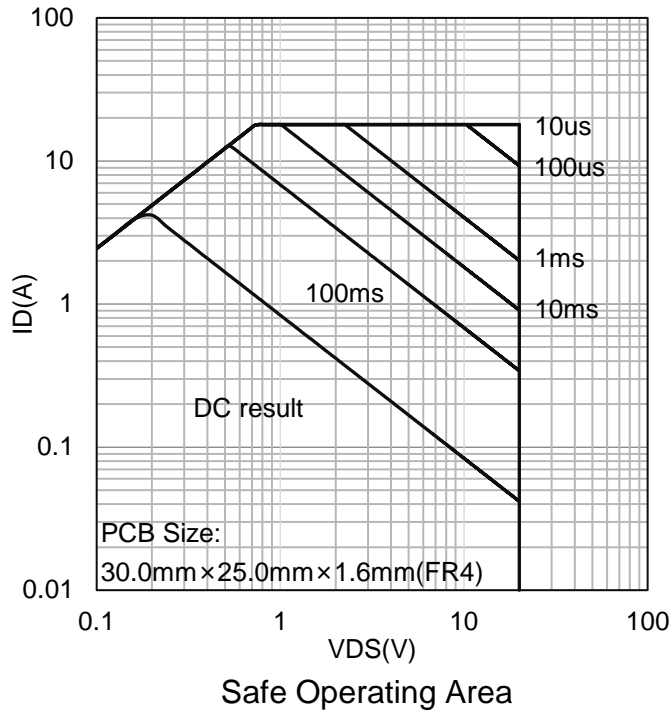
7. ELECTRICAL CHARACTERISTICS CURVES



7. ELECTRICAL CHARACTERISTICS CURVES(Con.)

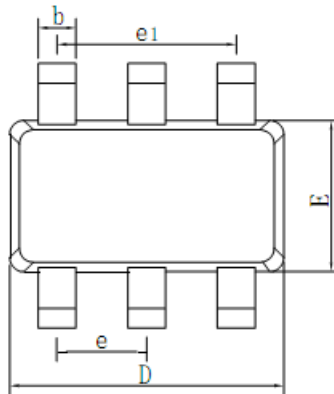
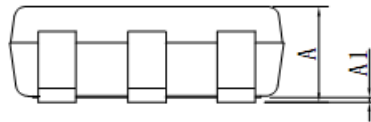
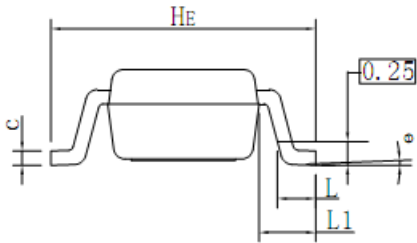


7. ELECTRICAL CHARACTERISTICS CURVES(Con.)



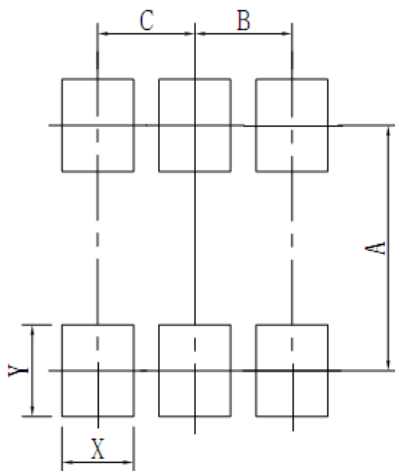
8. OUTLINE AND DIMENSIONS

SOT23-6



SOT23-6			
DIM	MIN	NOR	MAX
A	0.90	1.00	1.10
A1	0.01	0.06	0.10
b	0.25	0.40	0.50
c	0.10	0.17	0.26
D	2.80	2.90	3.10
E	1.30	1.60	1.70
e	0.85	0.95	1.05
e1	1.80	1.90	2.00
L	0.20	0.40	0.60
L1	0.60REF		
HE	2.50	2.80	3.00
θ	0°	-	10°

9. SOLDERING FOOTPRINT



SOT23-6	
DIM	(mm)
X	0.70
Y	0.90
A	2.40
B	0.95
C	0.95

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单击下面可查看定价，库存，交付和生命周期等信息

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